Unit in mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# HN4K03JU

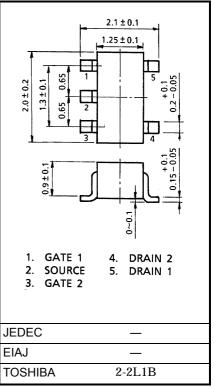
High Speed Switching Applications Analog Switch Applications

- High input impedance
- Low gate threshold voltage:  $V_{th} = 0.5 \sim 1.5 V$
- Excellent switching times
- Small package

#### Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit
Drain-Source voltage	$V_{DS}$	20	V
Gate-Source voltage	V <sub>GSS</sub>	10	V
DC Drain current	I <sub>D</sub>	100	mA
Drain power dissipation	P <sub>D</sub> *	200	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

<sup>\* :</sup> Total rating



Weight: 6.2mg

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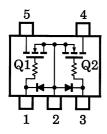
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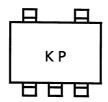
### Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0	_	_	1	μΑ
Drain-Source breakdown voltage		V (BR) DSS	I <sub>D</sub> = 100μA, V <sub>GS</sub> = 0	20	_	_	V
Drain cut-off curre	nt	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0	_	_	1	μΑ
Gate threshold vol	tage	V <sub>th</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 0.1mA	0.5	_	1.5	V
Forward transfer a	dmittance	Yfs	V <sub>DS</sub> = 3V, I <sub>D</sub> = 10mA	25	50	_	mS
Drain-Source ON resistance		R <sub>DS</sub> (ON)	I <sub>D</sub> = 10mA, V <sub>GS</sub> = 2.5V	_	8	12	Ω
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 3V, V <sub>GS</sub> = 0, f = 1MH <sub>z</sub>	_	8.5	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 3V, V <sub>GS</sub> = 0, f = 1MH <sub>z</sub>	_	3.3	_	pF
Output capacitance		Coss	V <sub>DS</sub> = 3V, V <sub>GS</sub> = 0, f = 1MH <sub>z</sub>	_	9.3	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3V, I_D = 10mA$ $V_{GS} = 0~2.5V$	_	0.16	_	
	Turn-off time	t <sub>off</sub>	$V_{DD} = 3V, I_D = 10mA$ $V_{GS} = 0~2.5V$	_	0.15	ı	μs

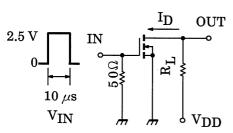
# **Equivalent Circuit (Top View)**

# Marking

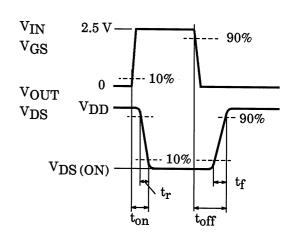


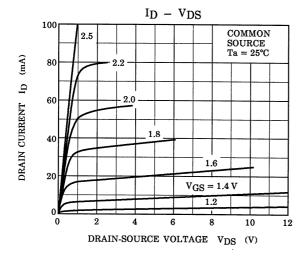


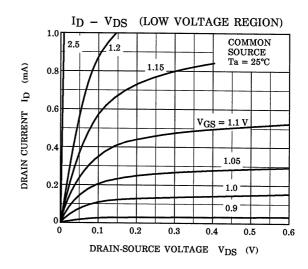
### (Q1, Q2 Common) Switching Time Test Circuit

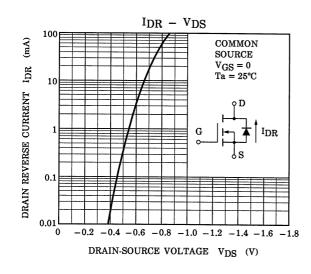


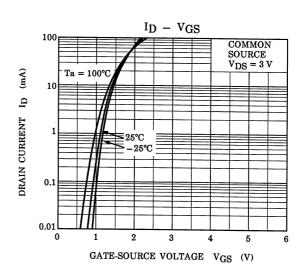
$$\begin{split} V_{DD} &= 3 \text{ V} \\ D.U. & \leqq 1\% \\ V_{IN} : t_r, \, t_f < 5 \text{ ns} \\ (Z_{out} &= 50 \, \Omega) \\ COMMON \text{ SOURCE} \\ Ta &= 25^{\circ}\text{C} \end{split}$$



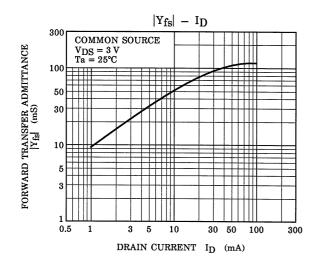


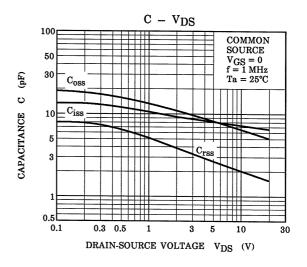


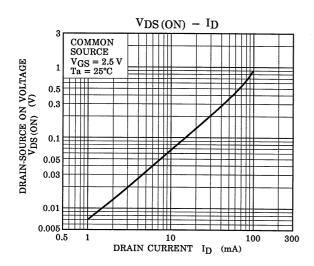


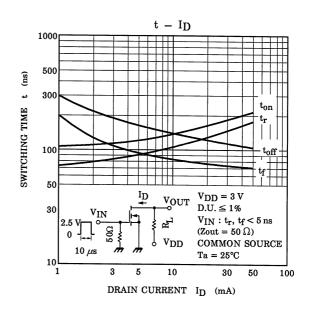


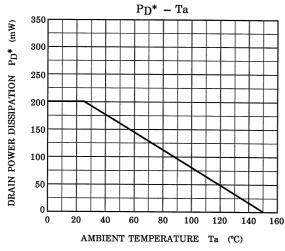
#### (Q1, Q2 Common)











\*: Total Rating